

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC2705

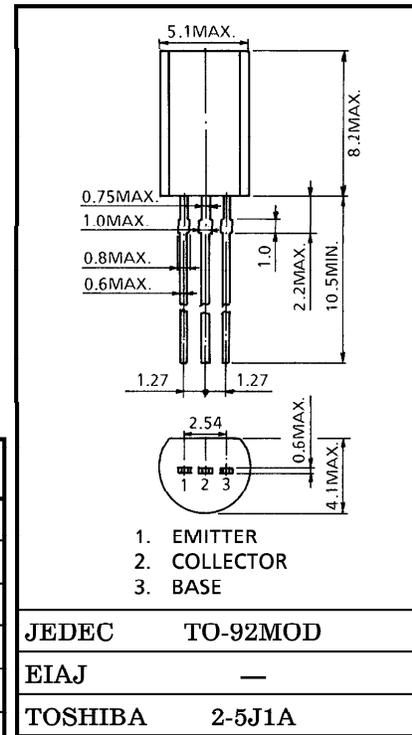
AUDIO FREQUENCY AMPLIFIER APPLICATIONS.

Unit in mm

- Complementary to 2SA1145.
- Small Collector Output Capacitance : $C_{ob} = 1.8\text{pF}$ (Typ.)
- High Transition Frequency : $f_T = 200\text{MHz}$ (Typ.)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Base Current	I_B	5	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



Weight : 0.36g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 150\text{V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	150	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	80	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$	—	—	1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	—	—	0.8	V
Transition Frequency	f_T	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	—	200	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	—	1.8	—	pF

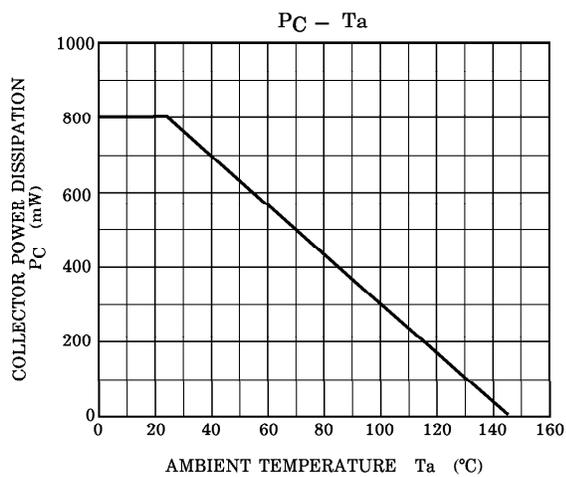
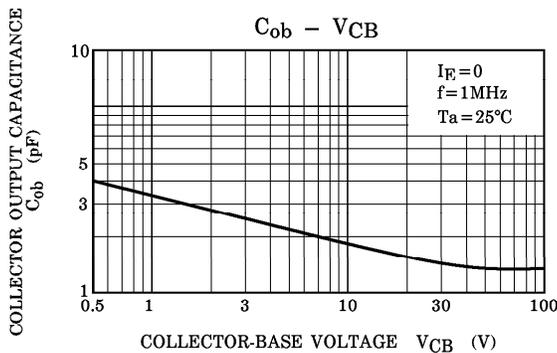
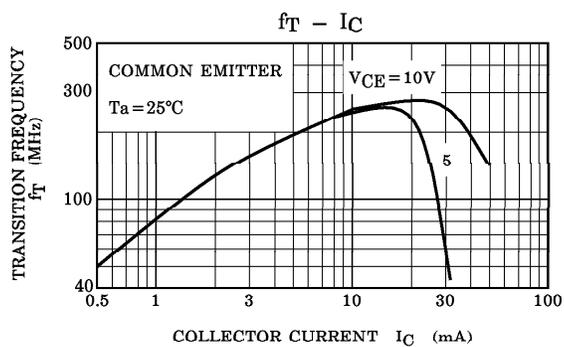
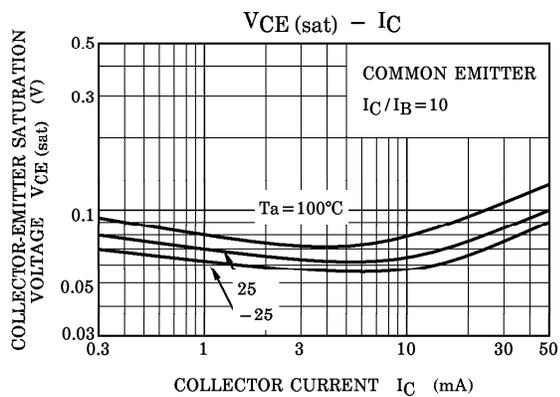
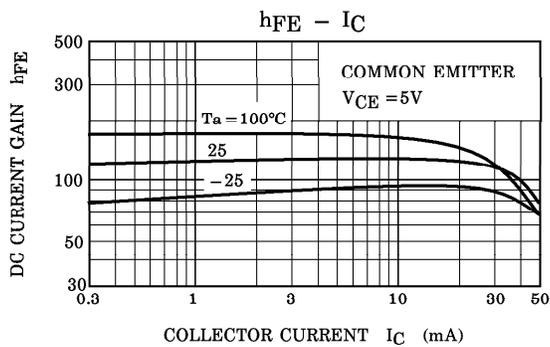
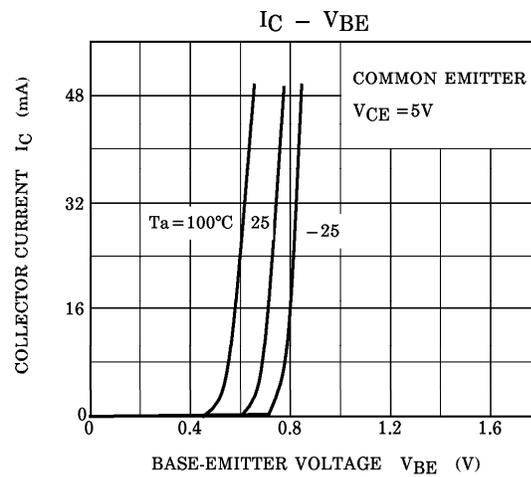
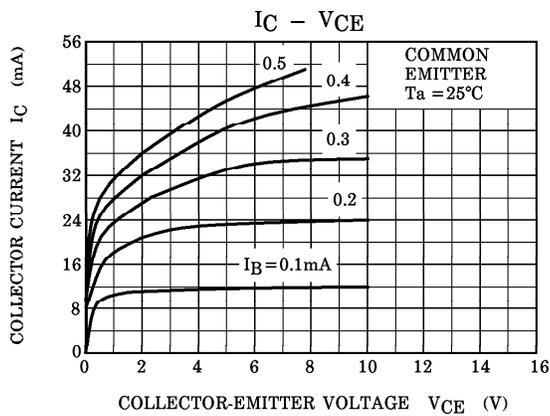
Note : h_{FE} Classification O : 80 ~ 160, Y : 120 ~ 240

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TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1145

Audio Frequency Amplifier Applications

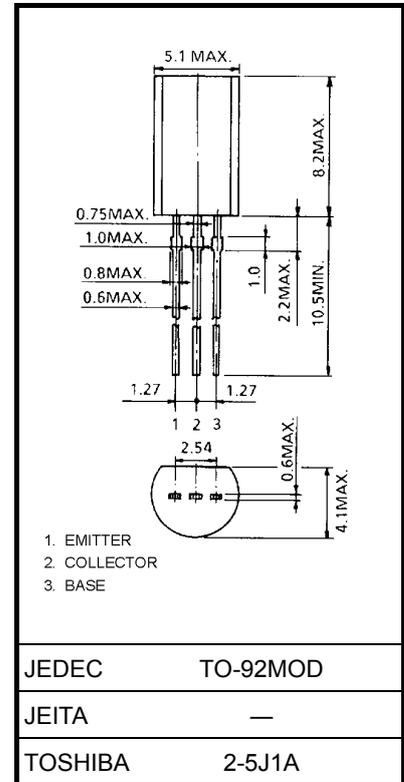
- Complementary to 2SC2705.
- Small Collector Output Capacitance: $C_{ob} = 2.5 \text{ pF}$ (typ.)
- High Transition Frequency: $f_T = 200 \text{ MHz}$ (typ.)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-150	V
Collector-emitter voltage	V_{CEO}	-150	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-50	mA
Base current	I_B	-5	mA
Collector power dissipation	P_C	800	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm



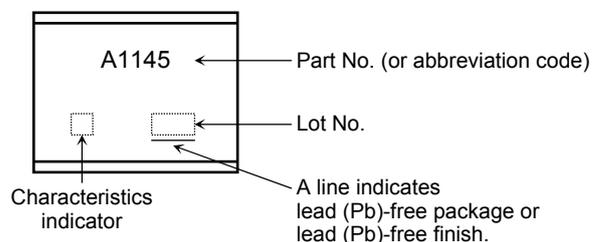
Weight: 0.36 g (typ.)

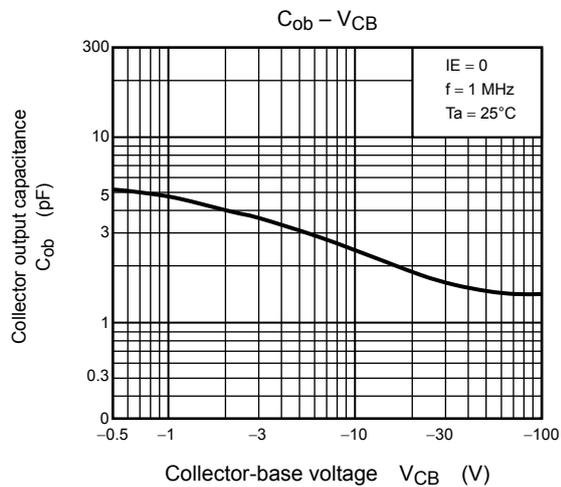
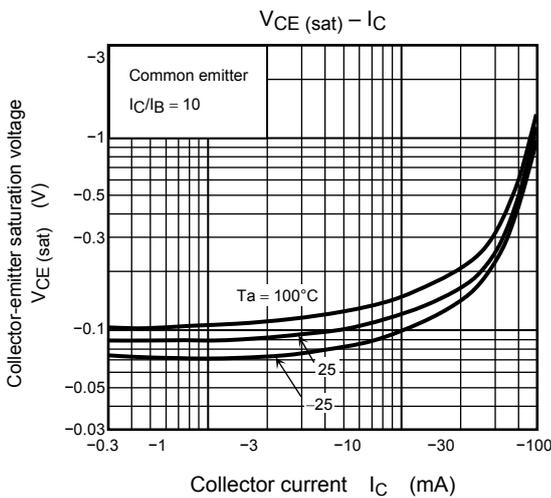
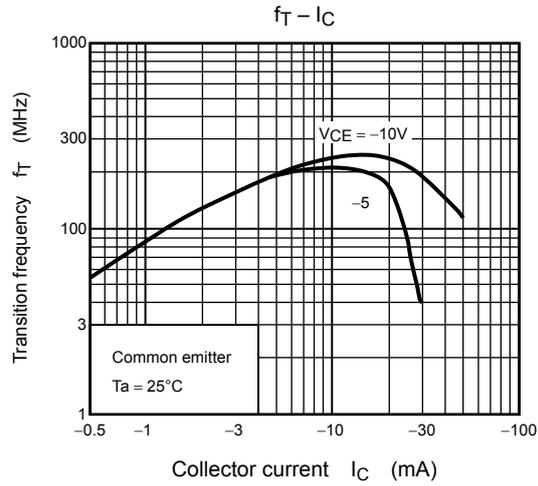
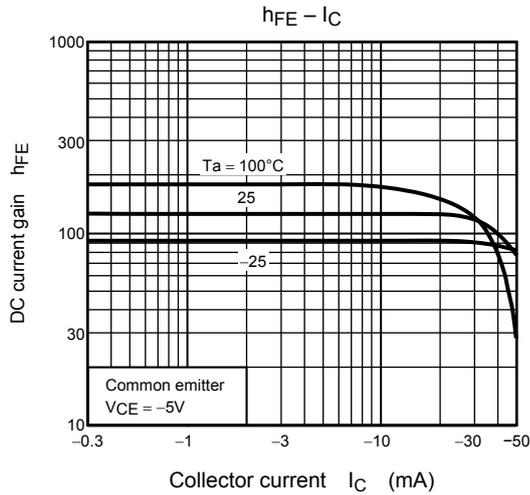
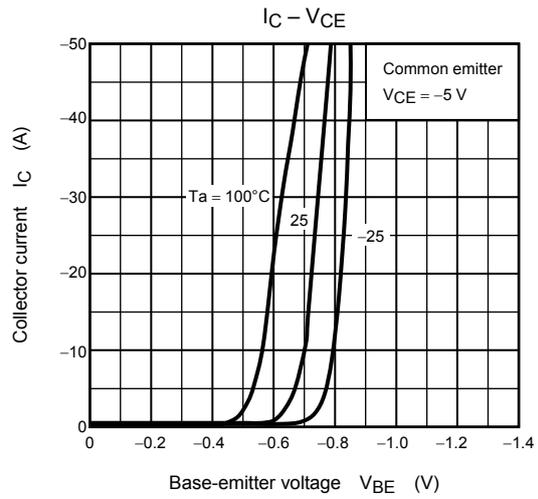
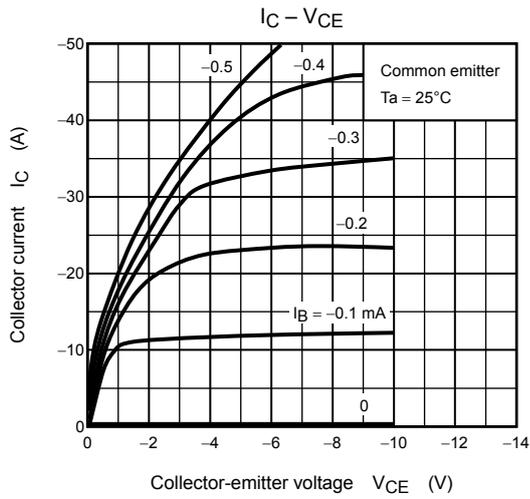
Electrical Characteristics (Ta = 25°C)

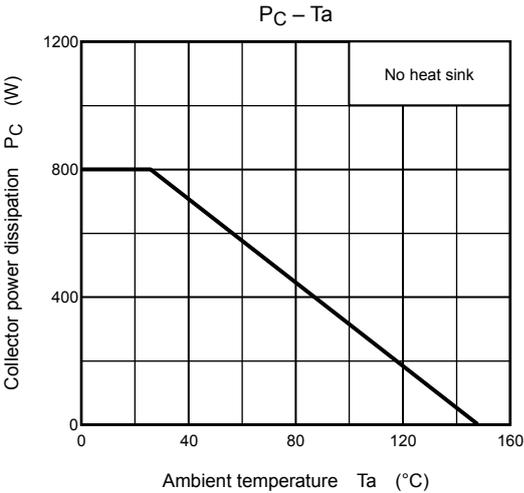
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -150\text{ V}, I_E = 0$	—	—	-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{ mA}, I_B = 0$	-150	—	—	V
DC current gain	h_{FE} (Note)	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	80	—	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$	—	—	-1.0	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	—	—	-0.8	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	—	200	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	2.5	—	pF

Note: h_{FE} classification O: 80 to 160, Y: 120 to 240

Marking







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